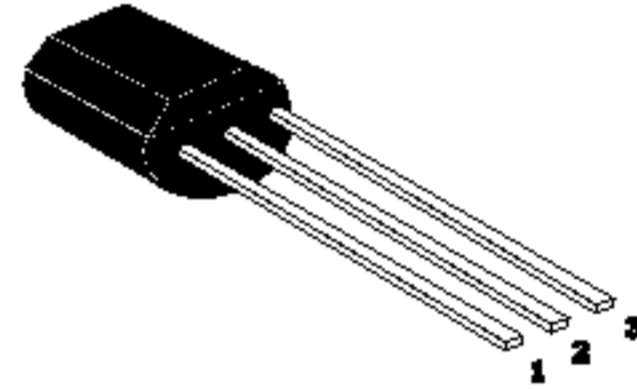




HIGH VOLTAGE TRANSISTOR

- * Collector-Emitter Voltage $V_{ce0}=400V$
- * Collector Dissipation $P_c(\text{Max})=625 \text{ mW}$ ($T_a=25^{\circ}C$)

Package: TO-92



2

ABSOLUTE MAXIMUM RATINGS at $T_{amb}=25^{\circ}C$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	500	V
Collector-Emitter Voltage	V_{ceo}	400	V
Emitter-Base Voltage	V_{ebo}	8	V
Collector Current	I_c	500	mA
Collector Dissipation	P_c	625	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~150	$^{\circ}C$

PIN:	1	2	3
STYLE	E	C	B
NO.1	E	C	B

ELECTRICAL CHARACTERISTICS at $T_{amb}=25^{\circ}C$

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{cbo}	500			V	$I_c=100\mu A$ $I_e=0$
Collector-Emitter Breakdown Voltage	BV_{ceo}	400			V	$I_c=1\text{mA}$ $I_b=0$
Emitter-Base Breakdown Voltage	BV_{ebo}	8			V	$I_e=100\mu A$ $I_c=0$
Collector Cutoff Current	I_{cbo}			10	μA	$V_{cb}=420V$ $I_e=0$
Emitter Cutoff Current	I_{ebo}			10	μA	$V_{eb}=8V$ $I_c=0$
DC Current Gain	H_{fe}	8		40		$V_{ce}=10V$ $I_c=5\text{mA}$
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			0.4	V	$I_c=50\text{mA}$ $I_b=10\text{mA}$
Base-Emitter Saturation Voltage	$V_{be(sat)}$			1	V	$I_c=50\text{mA}$ $I_b=10\text{mA}$
Current Gain-Bandwidth product	fT	10			MHz	$V_{ce}=10V$ $I_c=10\text{mA}$ $f=1\text{MHz}$